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	OTHER DEPARTMENTS	(Including Author, Title, D	ate, Pertinent Pages	s, Etc.)	
EXAMINER'S INITIALS					
BB	Ackmann, P., et al., "Phase Shifting and O Manufacturing for Sub 0.35 um I-Line", S			îces in	
Bb.	Lithas, "Lithas: Optical Proximity Correct	tion Software" (2 pages).			
Bb	Precim, "Proxima System", Precim Compa	any, Portland, Oregon (2 pages).			
BD	Precim, "Proxima Wafer Proximity Correc	tion System", Precim Company, Portla	nd, Oregon (2 pages).		
ВВ	Rieger, M., et al., "Mask Fabrication Rules for Proximity-Corrected Patterns", Precim Company, Portland, Oregon (10 pages).				
ВВ	Rieger, M., et al., "Using Behavior Modeli	ng for Proximity Correction", Precim C	Company, Portland, Oregon	(6 pages).	
BB	Cobb, et al., "Fast Sparse Aerial Image Ca	lculation for OPC", SPIE, Vol. 2621, p	p. 534-544, September 20-2	2, 1995.	
BB	Lucas, K., et al., "Model Based OPC for is	st Generation 193nm Lithography", Mc	otorola Inc., IDT assignee to	IMEC (12 p	ages).
BB	Stirniman, J., et al., "Quantifying Proximity and Related Effects in Advanced Wafer Processes", Precim Compnay, Hewlett Packard Labs (9 pages).				
BB	Sugawara, M., et al., "Practical Evaluation of Optical Proximity Effect Correction by EDM Methodology", Sony Corporation (11 pages).				
BO	Saleh, B., et al., "Reduction of Errors of Microphotographic Reproductions by Optimal Corrections of Original Masks", Optical Engineering, Vol. 20, No. 5, pp. 781-784, September/October 1981.				
Bo	Fu, C.C., et al., "Enhancement of Lithograp 38, No. 12, pp. 2599-2603, December 199		IEEE, Transactions On Elec	tron Device	s, Vol.
30	Harafuji, K., et al., "A Novel Hierarchical Approach for Proximity Effect Correction in Electron Beam Lithography", IEEE, Vol. 12, No. 10, pp. 1508-1514, October 1993.				
GH	Rieger, M., et al., "System for Lithography pages).	Proximity Compensation", Precim Co.	mpany, Portland, Oregon, So	eptember 19	93 (28

EXAMINER:	Bullon Benn	Date Considered:	3/3
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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		(Including Author, Title, I	Date, Pertinent Pages		
EXAMINER'S INITIALS	CITATION				
BB	Stirniman, J., et al., "Fast Proximity Corre-	ction with Zone Sampling", SPIE, Vo	1. 2197, pp. 294-301 (1994).		
BB	Stirniman, J., et al., "Optimizing Proximity Management, Vol. 2322, pp. 239-246 (199	Correction for Wafer Fabrication Pro 4).	ocesses", SPIE, Photomask To	echnology An	d
SB	Stirniman, J., et al., "Wafer Proximity Cor. 10-12, January 1994.	rection and Its Impact on Mask-Makin	ng", Bacus News, Vol. 10, Iss	sue 1, pp. 1, 3	-7,
BB	Henderson, R., et al., "Optical Proximity E (1994).	Effect Correction: An Emerging Techn	ology", Microlithography Wo	orld, pp. 6-12	
BO	Barouch, E., et al., "OPTIMASK: An OPC February 1995.	Algorithm for Chrome and Phase-Sh	ift Mask Design", SPIE, Vo.	2440, pp. 192	-206,
BB	Yen, A., et al., "Characterization and Corre Modeling", J. Vac. Sci. Technol. B, Vol. I			y Using Behav	vior
BB	Morimoto, H., et al., "Next Generation Ma Vol. 3236, pp. 188-189 (1997).	sk Strategy - Technologies are Ready	for Mass Production of 256M	IDRAM?", SI	PIE,
BB	Park, C., et al., "An Automatic Gate CD Co	ontrol for a Full Chip Scale SRAM De	evice", SPIE, Vol. 3236, pp	350-357 (199	7).
BB	Dolainsky, C., et al., "Application of a Sim (1997).	ple Resist Model to Fast Optical Prox	cimity Correction", SPIE, Vol	l. 3051, pp. 77	4-780
BB	Chuang, H., et al., "Practical Applications Logic Devices", IEEE, pp. 18.7.1-18.7.4, D	of 2-D Optical Proximity Corrections December 1997.	for Enhanced Performance of	f 0.25um Ran	dom
BB	Asai, N., et al., "Proposal for the Coma Ab Vol. 37, pp. 6718-6722 (1998).	erration Dependent Overlay Error Cor	mpensation Technology", Jpn	. J. Appl. Phy	s.,

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EXAMINER:	Benfor Bennen	Date Considered:	3/3/04

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	N. S.	& TRADEMARY OF	12/12/2001	283	25		
			REIGN PATENT DOCUM	IENTS			
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	YES	NO
154	JP 3-80525	4/5/1991	JP				
Br	WO 00/67074 A1	11/9/2000	wo				
GA	GB 2 324 169 A	10/14/1998	GB	1		Тп	ПП

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EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
Ba	5,631,110	5/20/1997	Shioiri, et al.	430	5	6/5/1995
BB	5,682,323	10/28/1997	Pasch, et al.	364	491	3/6/1995
BB	5,723,233	3/3/1998	Garza, et al.	430	5	2/27/1996
(50)	5,815,685	9/29/1998	Kamon	395	500	9/15/1995
(7P)	5,825,647	10/20/1998	Tsudaka	364	167.03	3/12/1996
BP	5,991,006	11/23/0199	Tsudaka	355	53	10/27/1997
DB.	6,081,658	6/27/2000	Rieger, et al.	395	500.22	12/31/1997
60	6,289,499	9/11/2001	Rieger, et al.	716	21	1/7/2000
BB	6,243,855 B1	6/5/2001	Kobayashi, et al.	716	19	9/29/1998
BIZ	6,249,597 B1	6/19/2001	Tsudaka	382	144	12/17/1998

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Filing Date

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U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
BO	6,014,456	1/11/2000	Tsudaka	382	144	7/15/1996
BB	6,154,563	11/28/2000	Tsudaka	382	144	12/17/1998
PB	6,298,473 B1	10/2/2001	Ono, et al.	716	21	12/3/1998
1517	6,453,457 B1	9/17/2002	Pierrat, et al.	716	19	9/29/2000
BB	2002/0100004 A1	7/25/2002	Pierrat, et al.	716	5	3/15/2002

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INFORMATION DISCLOSURE CITATION

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Serial No.

10/016,837

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITATION
BB	Cobb, N., et al., "Fast, Low-Complexity Mask Design", SPIE, Vol. 2440, pp. 313-327, February 22-24, 1995.
Bry	Cobb. N., et al., "Experimental Results on Optical Proximity Correction With Variable Threshold Resist Model", SPIE, Vol. 3051, pp. 458-468, March 12-14, 1997.
BB	Cohb. N., "Fast Optical and Process Proximity Correction Algorithms for Integrated Circuit Manufacturing", Dissertation, University of California at Berkeley, UMI Microform 9902038 (139 pages).
BO	Toublan, O., et al., "Phase Aware Proximity Correction for Advanced Masks", SPIE, Vol. 4000, pp. 160-170, March 1-3, 2000.
Br	Anonymous, "Parameterization For Full Shape And Rule Dependent Dissection", IPCOM000009587D, September 4, 2002 (9 pages).

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